

# 2SK2730

Silicon N Channel MOS FET  
High Speed Power Switching

# HITACHI

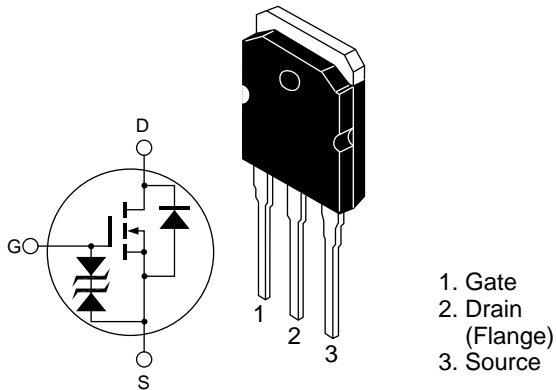
ADE-208-493 A  
2nd. Edition

## Features

- Low on-resistance
- High speed switching
- Low drive current
- Avalanche ratings

## Outline

TO-3P



**Absolute Maximum Ratings** ( $T_a = 25^\circ\text{C}$ )

<b>Item</b>	<b>Symbol</b>	<b>Ratings</b>	<b>Unit</b>
Drain to source voltage	$V_{DSS}$	500	V
Gate to source voltage	$V_{GSS}$	$\pm 30$	V
Drain current	$I_D$	25	A
Drain peak current	$I_{D(pulse)}^{*1}$	100	A
Body to drain diode reverse drain current	$I_{DR}$	25	A
Avalanche current	$I_{AP}^{*3}$	25	A
Avalanche energy	$E_{AR}^{*3}$	35	mJ
Channel dissipation	$Pch^{*2}$	175	W
Channel temperature	Tch	150	$^\circ\text{C}$
Storage temperature	Tstg	-55 to +150	$^\circ\text{C}$

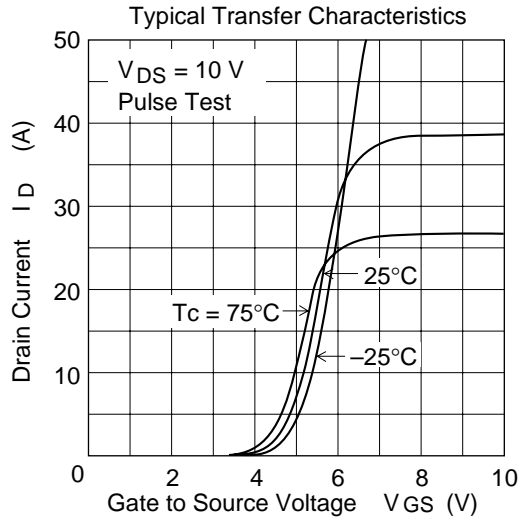
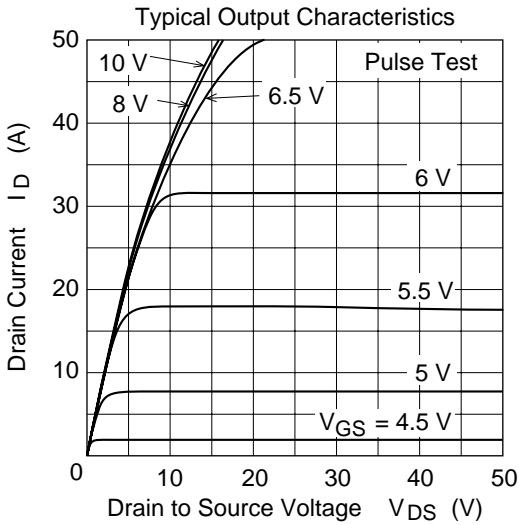
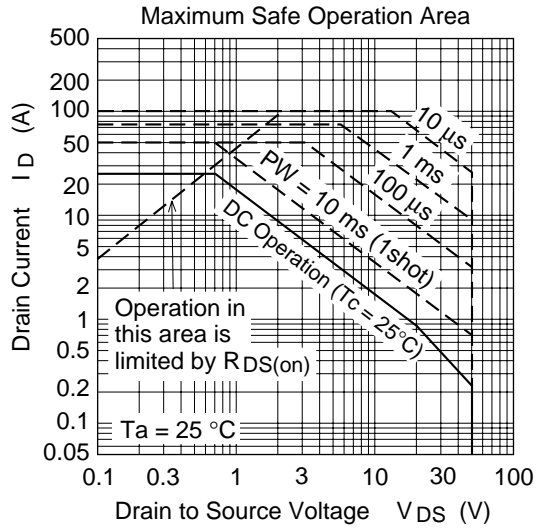
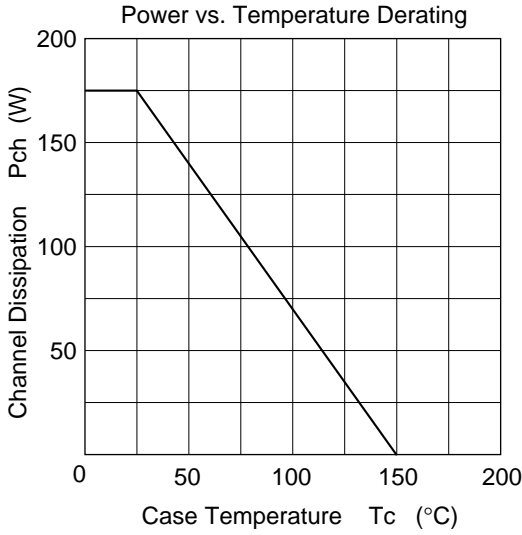
- Notes: 1.  $PW \leq 10\mu\text{s}$ , duty cycle  $\leq 1\%$   
2. Value at  $T_c = 25^\circ\text{C}$   
3. Value at  $Tch = 25^\circ\text{C}$ ,  $R_g = 50\Omega$ ,  $L = 100\mu\text{H}$

## Electrical Characteristics (Ta = 25°C)

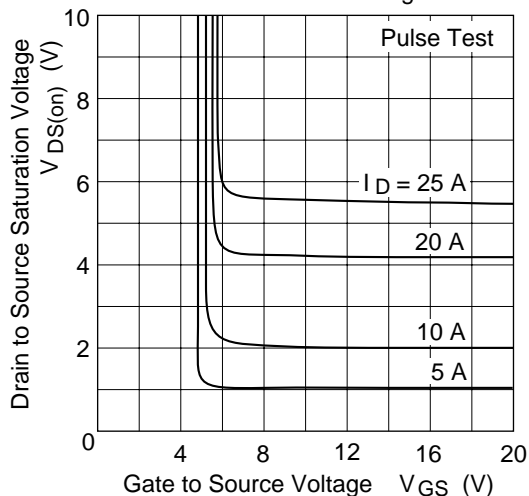
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	500	—	—	V	$I_D = 10\text{mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±30	—	—	V	$I_G = \pm 100\mu\text{A}, V_{DS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	±10	μA	$V_{GS} = \pm 25\text{V}, V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	10	μA	$V_{DS} = 500\text{V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.5	—	3.5	V	$I_D = 1\text{mA}, V_{DS} = 10\text{V}^{*1}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.2	0.24	Ω	$I_D = 15\text{A}, V_{GS} = 10\text{V}^{*1}$
Forward transfer admittance	$ y_{fs} $	12	20	—	S	$I_D = 15\text{A}, V_{DS} = 10\text{V}^{*1}$
Input capacitance	$C_{iss}$	—	3500	—	pF	$V_{DS} = 10\text{V}$
Output capacitance	$C_{oss}$	—	1000	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	$C_{rss}$	—	150	—	pF	$f = 1\text{MHz}$
Total gate charge	$Q_g$	—	65	—	nc	$V_{DD} = 400\text{V}$
Gate to source charge	$Q_{gs}$	—	16	—	nc	$V_{GS} = 10\text{V}$
Gate to drain charge	$Q_{gd}$	—	24	—	nc	$I_D = 25\text{A}$
Turn-on delay time	$t_{d(on)}$	—	50	—	ns	$V_{GS} = 10\text{V}, I_D = 15\text{A}$
Rise time	$t_r$	—	140	—	ns	$R_L = 2\Omega$
Turn-off delay time	$t_{d(off)}$	—	200	—	ns	
Fall time	$t_f$	—	110	—	ns	
Body to drain diode forward voltage	$V_{DF}$	—	1.1	—	V	$I_D = 25\text{A}, V_{GS} = 0$
Body to drain diode reverse recovery time	$t_{rr}$	—	450	—	ns	$I_F = 25\text{A}, V_{GS} = 0$ $diF/dt = 100\text{A}/\mu\text{s}$

Note: 1. Pulse test

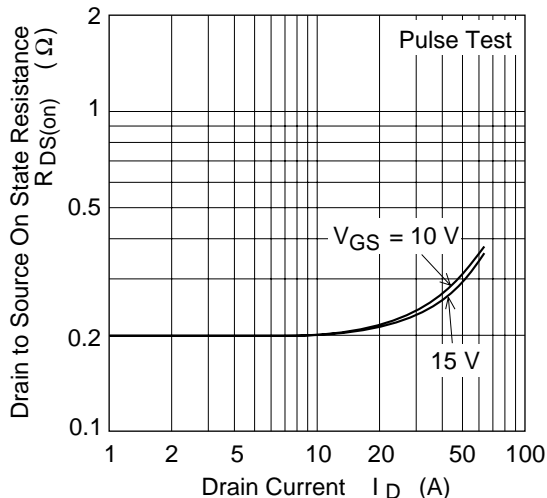
Main Characteristics



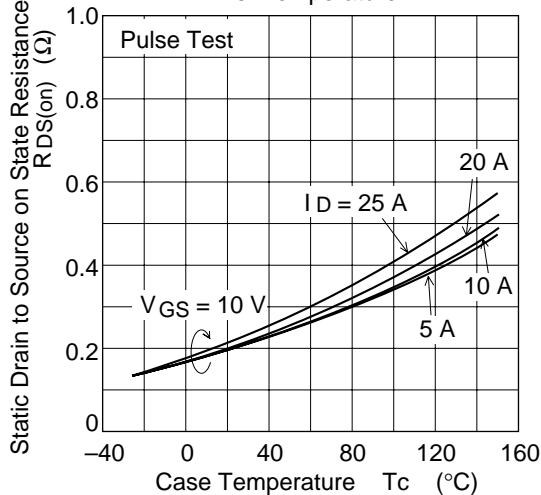
Drain to Source Saturation Voltage vs. Gate to Source Voltage



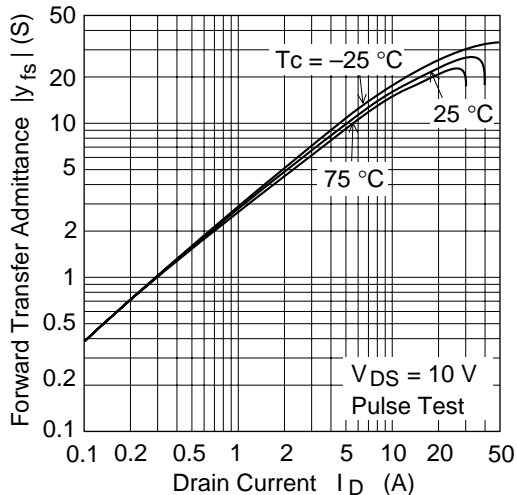
Static Drain to Source on State Resistance vs. Drain Current



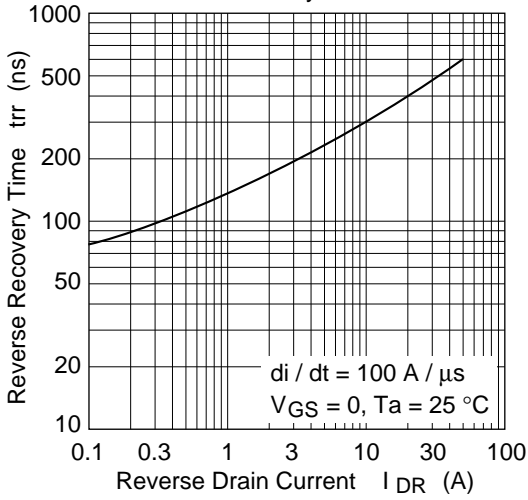
Static Drain to Source on State Resistance vs. Temperature



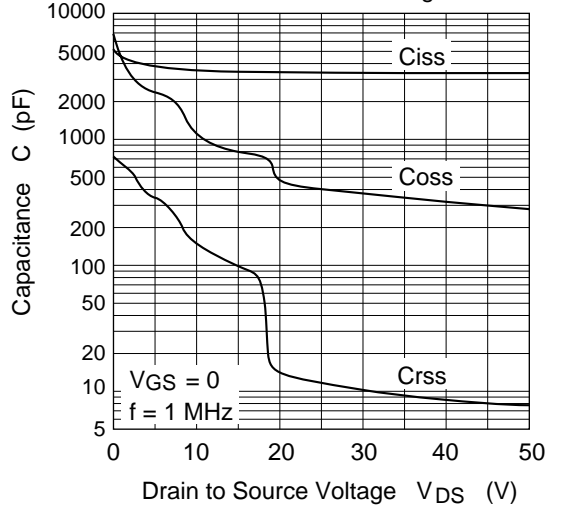
Forward Transfer Admittance vs. Drain Current



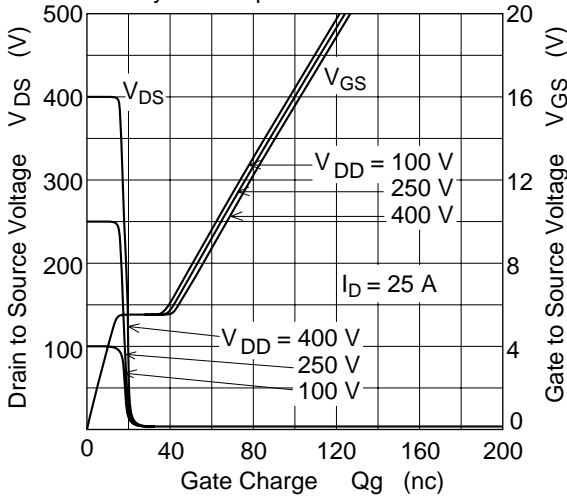
Body to Drain Diode Reverse Recovery Time



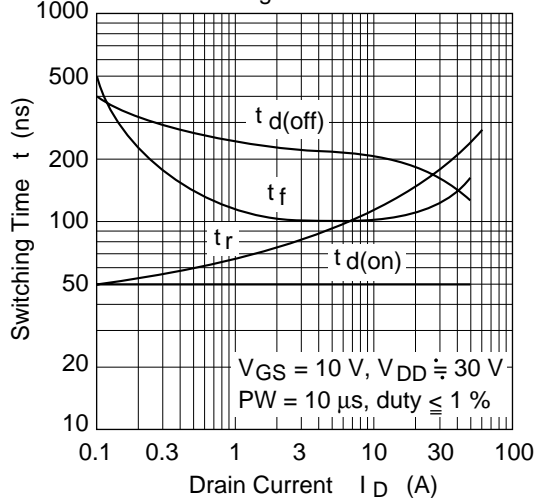
Typical Capacitance vs. Drain to Source Voltage

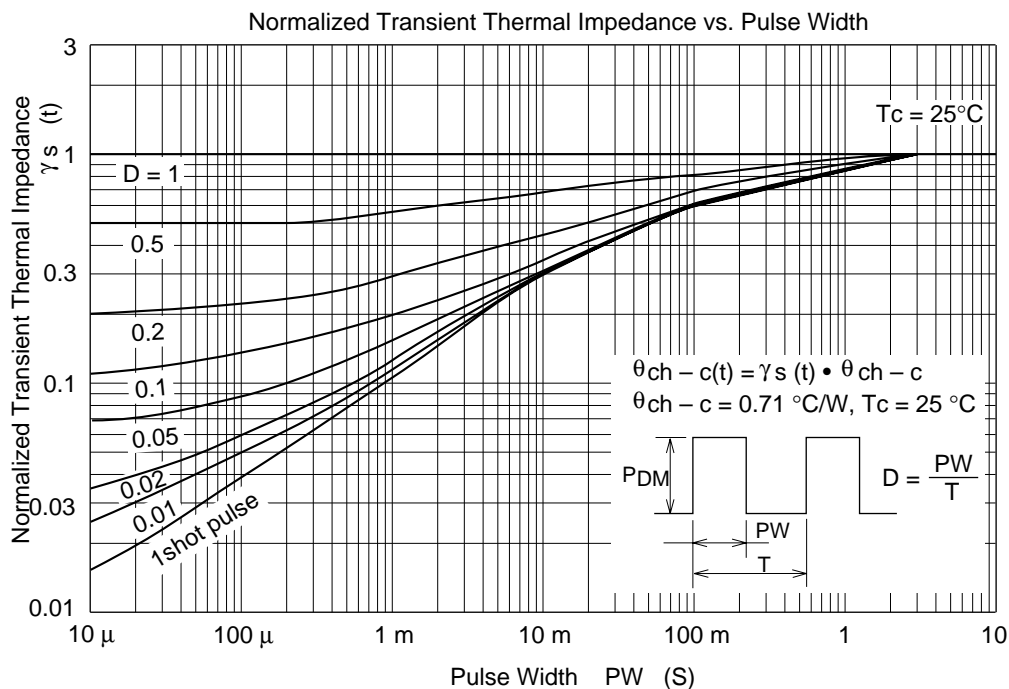
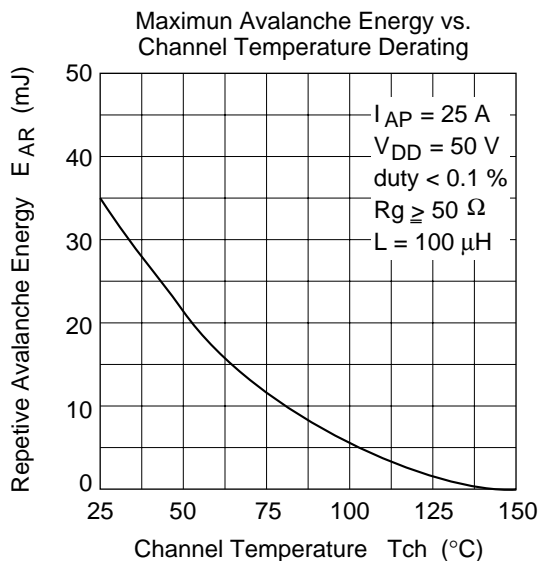
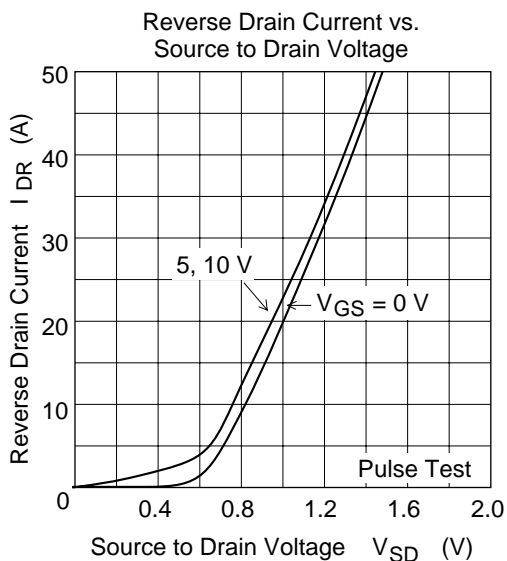


Dynamic Input Characteristics

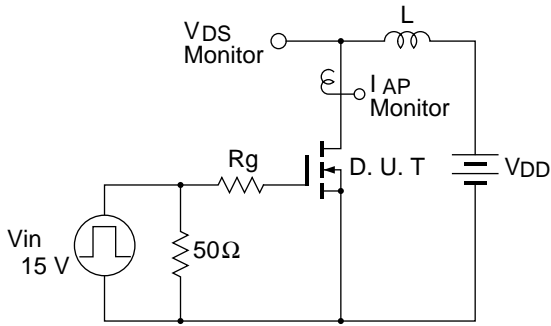


Switching Characteristics



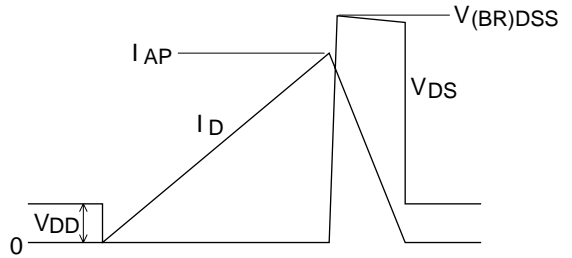


Avalanche Test Circuit

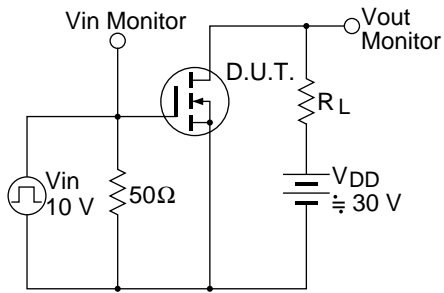


Avalanche Waveform

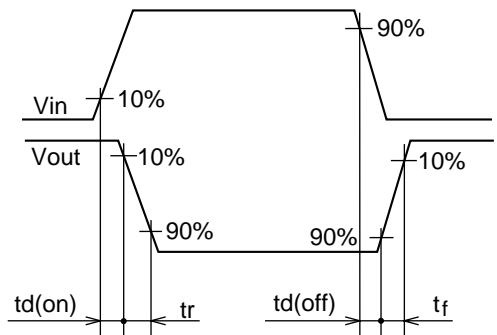
$$E_{AR} = \frac{1}{2} \cdot L \cdot I_{AP}^2 \cdot \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$



Switching Time Test Circuit



Switching Time Waveform







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